

1/6

100

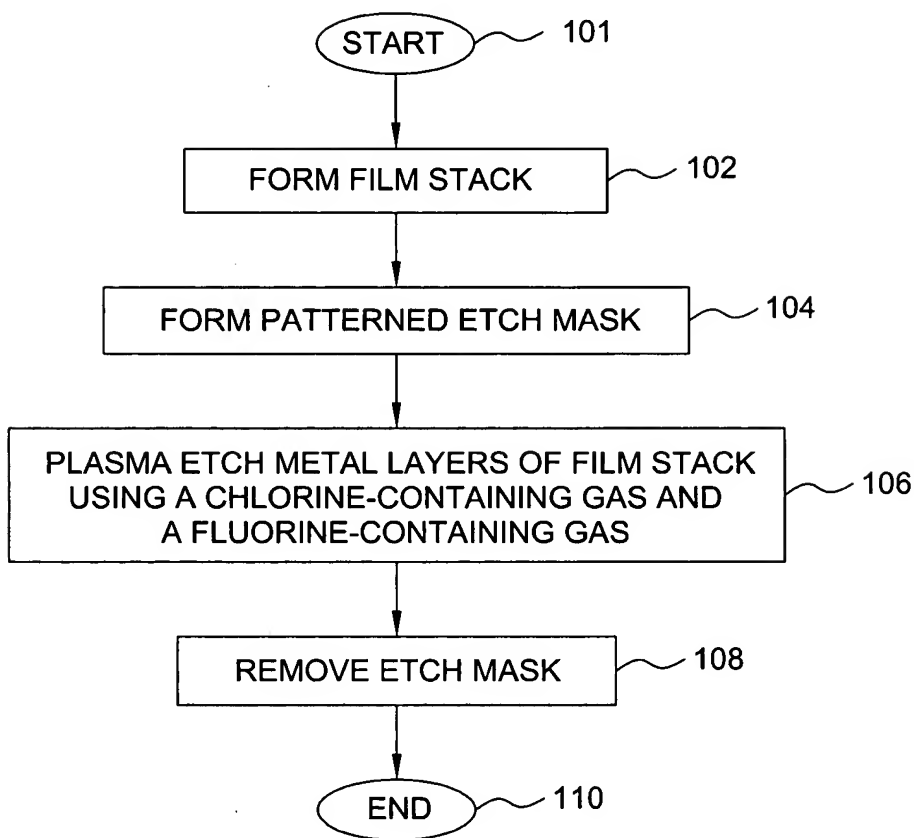


FIG. 1

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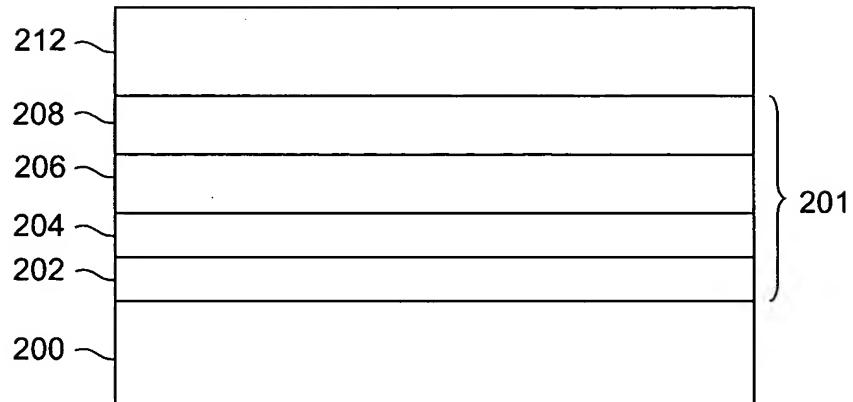


FIG. 2A

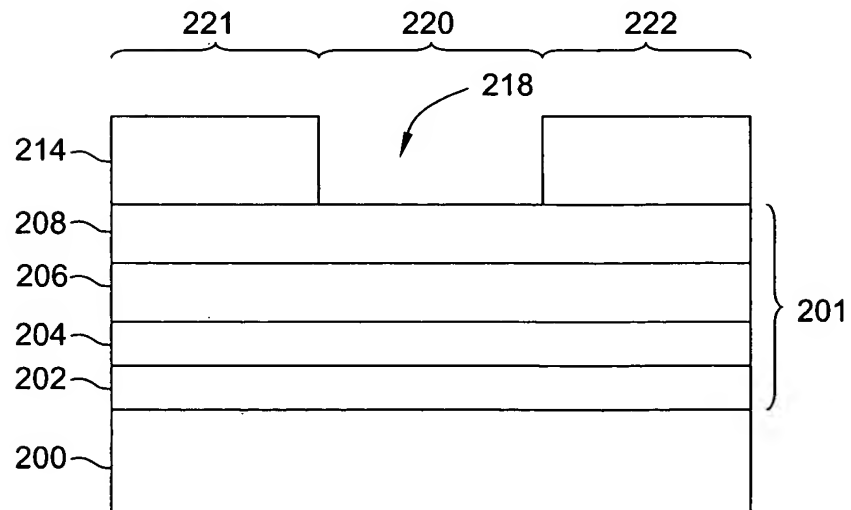


FIG. 2B

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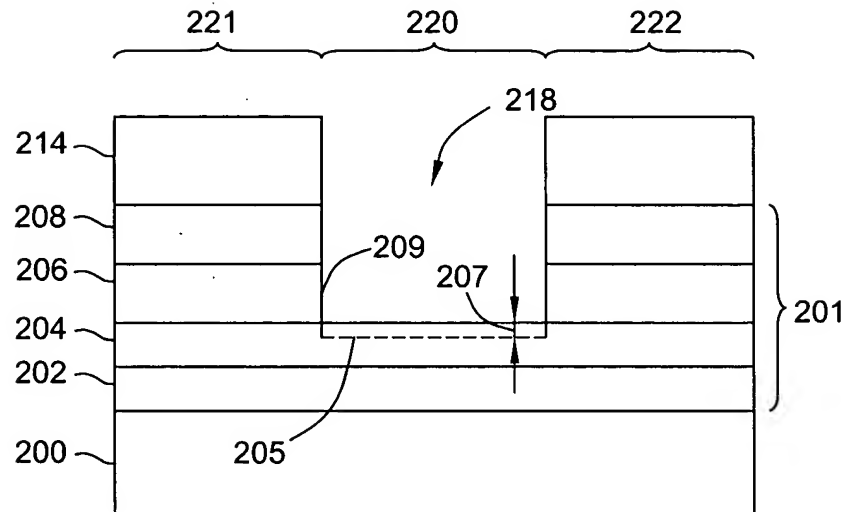


FIG. 2C

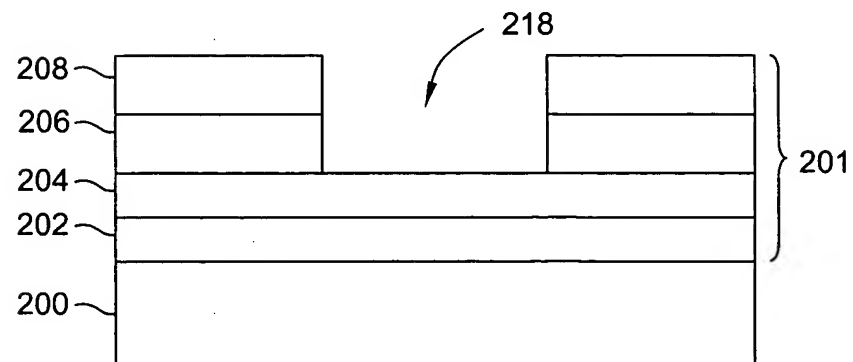


FIG. 2D

300

310

EMBODIMENTS OF A FILM STACK OF A RESISTIVE HEADER DEVICE				
LAYER OF FILM STACK	FILM STACK CONFIGURATIONS			
	A	B	C	D
FIRST CONDUCTIVE LAYER	Nb	Ta	Ta	Nb
SECOND CONDUCTIVE LAYER	Ti	Nb	Ti	none
FIRST DIELECTRIC LAYER	SiC	SiC	SiC	SiC
SECOND DIELECTRIC LAYER	Si <sub>3</sub> N <sub>4</sub>	Si <sub>3</sub> N <sub>4</sub>	Si <sub>3</sub> N <sub>4</sub>	Si <sub>3</sub> N <sub>4</sub>

FIG. 3

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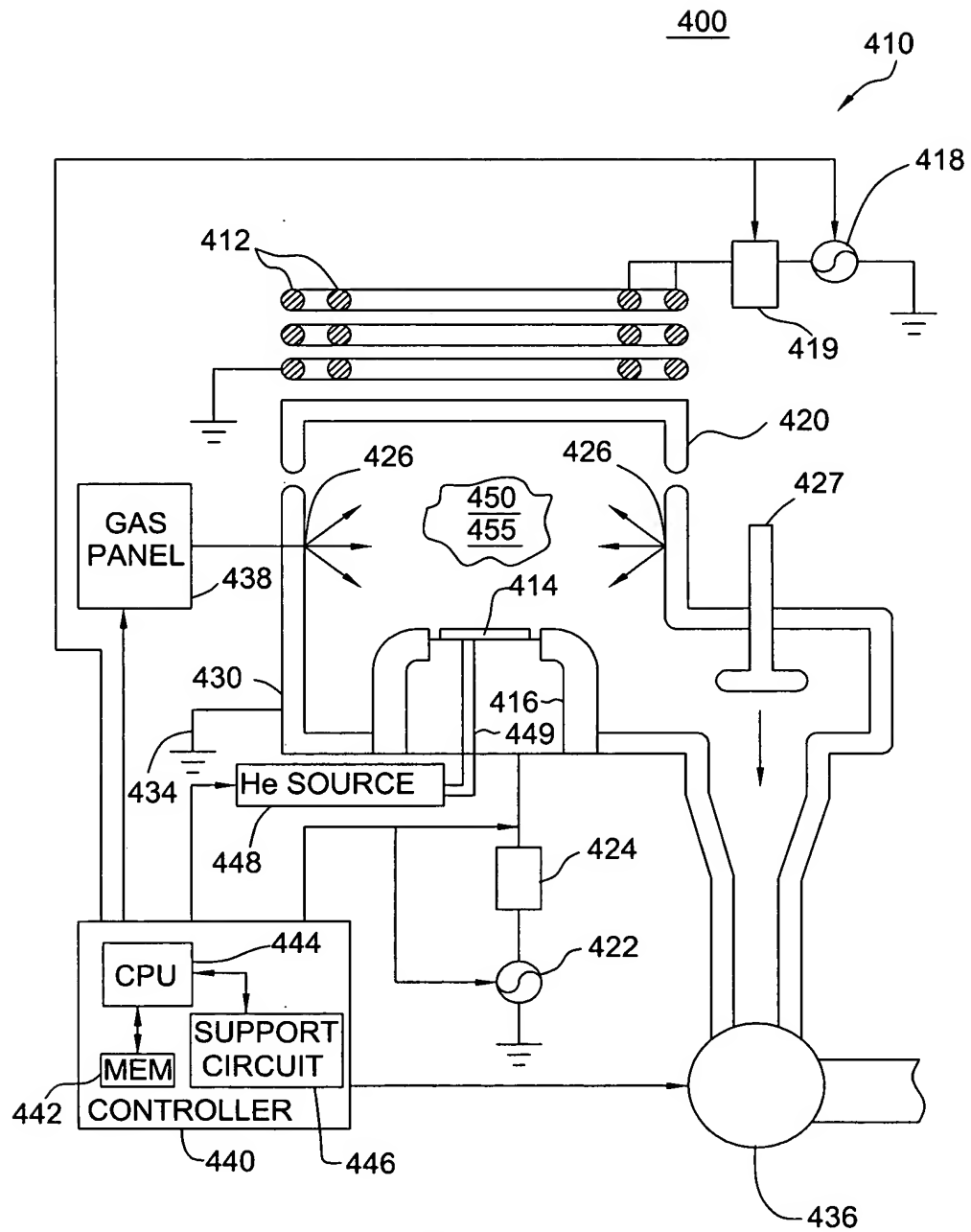


FIG. 4

502	PLASMA ETCH PROCESS OF THE PRESENT INVENTION	504	506
PARAMETER	PROCESS RANGES	EXAMPLE	
	UNITS	MIN	MAX
CHLORINE (Cl <sub>2</sub> )	SCCM	10	300
CARBON TETRAFLUORIDE (CF <sub>4</sub> )	SCCM	10	300
CHAMBER PRESSURE	mTorr	2	50
SUBSTRATE TEMPERATURE	DEGREES CELSIUS	10	80
SUBSTRATE BIAS POWER	W	0	500
PLASMA POWER	W	200	3000

FIG. 5